

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Original): A bulk acoustic wave device comprising:

a bulk acoustic wave element including a piezoelectric layer formed on a substrate, a lower electrode contacting a lower surface of the piezoelectric layer, and an upper electrode contacting an upper surface of the piezoelectric layer and partially overlapping the lower electrode, a lower hollow section being formed between the substrate and the lower surface of the piezoelectric layer, a first through-hole reaching the lower hollow section being formed through the bulk acoustic element in a direction perpendicular to a surface of the piezoelectric layer;

an upper hollow section forming layer forming an upper hollow section with the upper surface of the piezoelectric layer, a second through-hole reaching the upper hollow section being formed therethrough in a direction perpendicular to a surface thereof; and

a sealing layer covering the upper hollow section forming layer and filling up the second through-hole.

Claim 2 (Original): The bulk acoustic wave device according to claim 1, wherein the first through-hole and the second through-hole overlap each other.

Claim 3 (Original): The bulk acoustic wave device according to claim 1, wherein edge portions of the piezoelectric layer are flat, the piezoelectric layer is spaced incrementally apart from the substrate from the edge portions toward a central portion, the central portion is flat, and overlapping portions of the lower electrode and the upper electrode is located at the flat portion of the central portion.

Claim 4 (Original): The bulk acoustic wave device according to claim 1, wherein at least a surface of the sealing layer is formed of a metal.

Claim 5 (Original): A bulk acoustic wave device comprising:

a bulk acoustic wave element including a piezoelectric layer formed on a substrate, on which a recess is formed, a lower electrode contacting a lower surface of the piezoelectric layer, and an upper electrode contacting an upper surface of the piezoelectric layer and partially overlapping the lower electrode, a lower hollow section being formed between the recess of the substrate and the lower surface of the piezoelectric layer, a first through-hole reaching the lower hollow section being formed through the bulk acoustic wave element in a direction perpendicular to a surface of the piezoelectric layer;

an upper hollow section forming layer forming an upper hollow section with the upper surface of the piezoelectric layer, a second through-hole reaching the upper hollow section being formed therethrough in a direction perpendicular to a surface thereof; and

a sealing layer covering the upper hollow section forming layer and filling up the second through-hole.

Claim 6 (Original): The bulk acoustic wave device according to claim 5, wherein the piezoelectric layer is flat.

Claim 7 (Original): The bulk acoustic wave device according to claim 5, wherein at least a surface of the sealing layer is formed of a metal.

Claim 8 (Original): A bulk acoustic wave device comprising:

an acoustic reflection layer formed on a substrate;

a bulk acoustic wave element including a piezoelectric layer covering the acoustic reflection layer, a lower electrode contacting a lower surface of the piezoelectric layer, and an upper electrode contacting an upper surface of the piezoelectric layer and partially overlapping the lower electrode;

a hollow section forming layer forming a hollow section with the upper surface of the piezoelectric layer, a through-hole reach the hollow section being formed in a direction perpendicular to a surface of the hollow section forming layer; and

a sealing layer covering the hollow section forming layer and filling up the through-hole.

Claim 9 (Original): The bulk acoustic wave device according to claim 8, wherein the piezoelectric layer is flat.

Claim 10 (Original): The bulk acoustic wave device according to claim 8, wherein the acoustic reflection layer is a Bragg acoustic reflection layer.

Claim 11 (Original): The bulk acoustic wave device according to claim 8, wherein the acoustic reflection layer is embedded in the substrate.

Claim 12 (Original): The bulk acoustic wave device according to claim 8, wherein at least a surface of the sealing layer is formed of a metal.

Claims 13- 15 (Canceled)